



#### **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
-25V	10Ω @ V <sub>GS</sub> = -4.5V	-150mA		
	13Ω @ V <sub>G</sub> S = -2.7V	-140mA		

## **Description**

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

## **Features and Benefits**

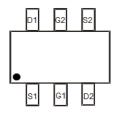
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

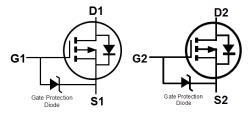
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)









Top View

Top View Equivalent Circuit

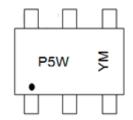
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMG6302UDW-7	SOT363	3,000/Tape & Reel
DMG6302UDW-13	SOT363	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



P5W = Product Type Marking Code YM or  $\overline{Y}$ M = Date Code Marking Y or  $\overline{Y}$  = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	ı	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings – Total Device (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	310	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	407	°C/W
Power Dissipation (Note 6)	PD	380	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	326	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Maximum Ratings P-CHANNEL (@TA = +25°C, unless otherwise specified.)

Characteris	stic		Symbol	Value	Unit
Drain-Source Voltage			VDSS	-25	V
Gate-Source Voltage	(	Continuous	Vgss	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-150 -120	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = -2.7V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	-140 -110	mA

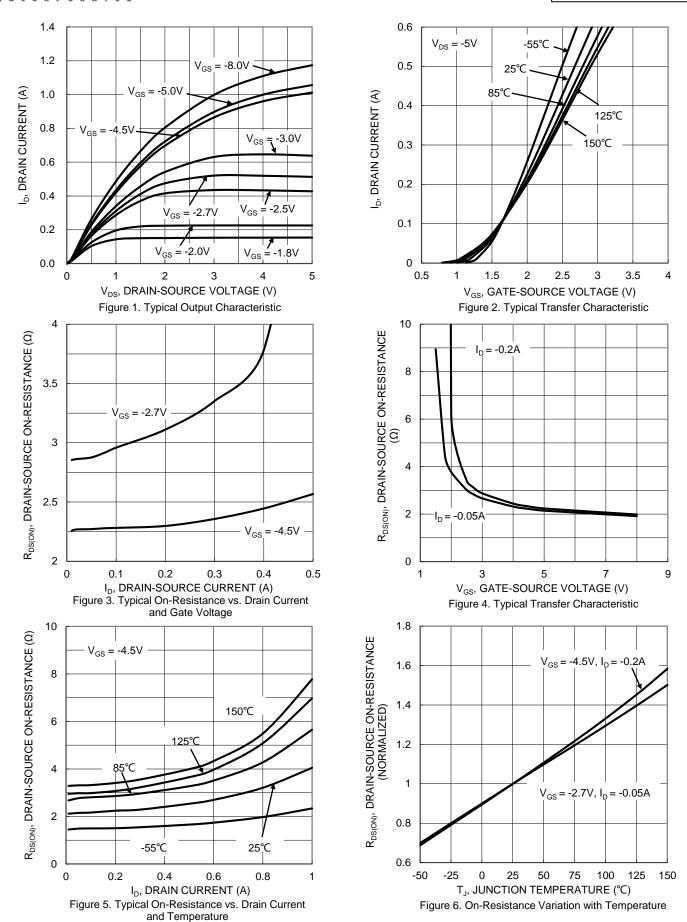
## Electrical Characteristics P-CHANNEL (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Oymbor	141111	1 )	mux	Oint	rest condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-25	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_		-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	Igss	_		-100	nA	$V_{GS} = -8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)		•		•	•		
Gate Threshold Voltage	Vgs(TH)	-0.65	_	-1.5	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Dagger	_	2	10	Ω	$V_{GS} = -4.5V$ , $I_D = -0.14A$	
Static Drain-Source On-Resistance	RDS(ON)	_	2.7	13	Ω	$V_{GS} = -2.7V, I_{D} = -0.05A$	
Diode Forward Voltage	VsD	_	-0.8	-1.2	V	$V_{DS} = V_{GS}$ , $I_D = -0.2A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	30.7	_		V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	5.9	_	pF		
Reverse Transfer Capacitance	Crss	_	1.5	_			
Total Gate Charge	Qg	_	0.34	_			
Gate-Source Charge	Qgs	_	0.06	_	nC	V <sub>DS</sub> = -5V, I <sub>D</sub> = -0.2A, V <sub>GS</sub> = -4.5V	
Gate-Drain Charge	Qgd	_	0.08	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.3	_			
Turn-On Rise Time	t <sub>R</sub>	_	2.0	_	ns	$V_{GS} = -4.5V, V_{DD} = -6V$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16.3	_	115	$I_D = -0.2A, R_G = 50\Omega$	
Turn-Off Fall Time	tF	_	7.9	_			

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1"  $\times$  1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







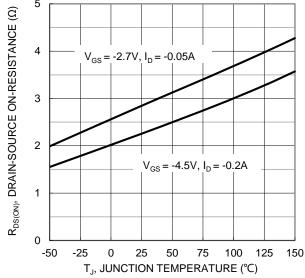
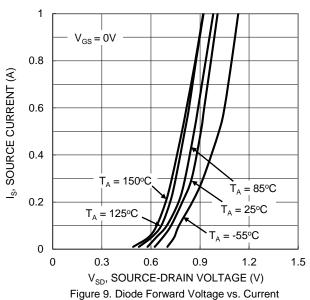


Figure 7. On-Resistance Variation with Temperature

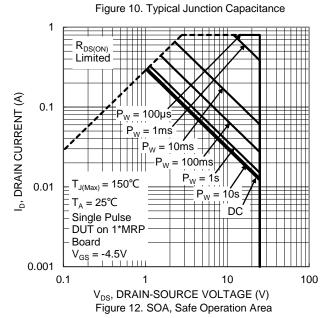


10 8 6  $V_{GS}(V)$ 4  $V_{DS} = -5V, I_D = -0.2A$ 2 0 0 0.1 0.2 0.3 0.4 0.5 0.6 0.7 8.0 Q<sub>q</sub> (nC)

Figure 11. Gate Charge

1.5  $V_{GS(TH)},$  GATE THRESHOLD VOLTAGE (V) 1.3 1.1  $I_D = -1mA$ 0.9  $I_D = -250 \mu A$ 0.7 0.5 -50 -25 0 25 50 75 100 125 150 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction

Temperature 1000 f = 1MHzC<sub>T</sub>, JUNCTION CAPACITANCE (pF) 100  $C_{iss}$ 10 1  $C_{rss}$ 0 0 10 15 20 25 30 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)





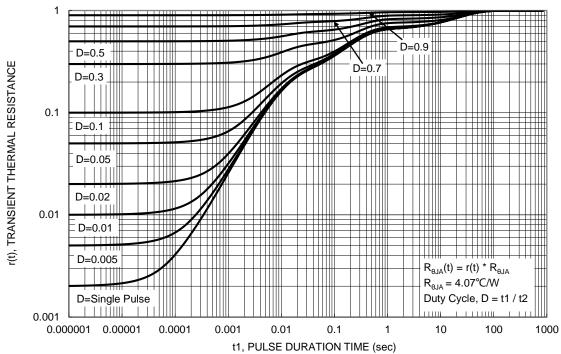


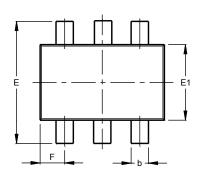
Figure 13. Transient Thermal Resistance

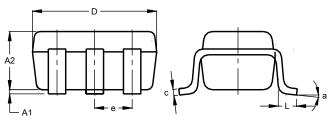


# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



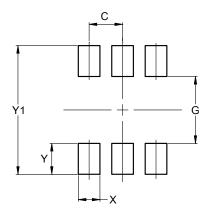


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
E	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



Dimensions	Value			
Dillicitatoria	(in mm)			
С	0.650			
G	1.300			
Х	0.420			
Y	0.600			
Y1	2.500			



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### **LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com